

# Phase pure fullerene based superconducting thin films: in-situ growth and ultra-high vacuum Raman characterization.

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Thin films of organic superconductors (SCs) are an attractive platform for studying the effects of doping, layer thickness and substrate on the superconducting (SC) transition temperature and the SC mechanism. The fullerene-based family of  $A_3C_{60}$  (A is an alkali metal) SCs is of particular interest because of their high critical temperature ( $Rb_3C_{60}$  has  $T_c=30.9$  K) and weak van-der-Waals interaction between the molecular film and the substrate. It has been shown that thin films of  $C_{60}$  grow epitaxially on topological insulators [1] and  $K_3C_{60}$  has been synthesized on a semiconductor surface [2]. Amongst the alkali metal intercalated fullerenes, only the  $A_3C_{60}$  phase is superconducting. However, it can co-exist with other phases such as the insulating  $A_6C_{60}$  phase and can form non-stoichiometric phases. Thus, achieving phase purity is an important open problem in the growth of thin films of organic SCs which needs to be solved e.g. for achieving proximity induced SC. Moreover,  $A_3C_{60}$  is air-sensitive and hence it must be studied in an ultra-high vacuum (UHV) environment. Raman is amongst the most direct methods that reveal the phase but the air sensitivity of  $A_xC_{60}$  precludes the application of standard Raman that is carried out in air or in high vacuum. Here, we apply the UHV Raman technique to achieve growth of phase pure SC  $Rb_3C_{60}$  films that we perform in a home built optical chamber down to  $T=4.2$ K. We perform the full sample preparation (sputtering, annealing, and  $Rb_3C_{60}$  growth) and characterization (electron diffraction and UHV-Raman) in-situ [3]. It is found that even  $\sim 2$ -3 monolayers of  $Rb_3C_{60}$  have a sufficiently strong Raman response that can easily be measured inside UHV within several minutes. The stoichiometry of the thin film can be accurately controlled in-situ by tracking its Raman response. That is, the main Raman peak of  $C_{60}$  is at  $1460\text{cm}^{-1}$ , while in the case of  $Rb_3C_{60}$ , the peak moves to  $1450\text{cm}^{-1}$ . Finally, for  $Rb_6C_{60}$ , the peak shifts down further to  $1435\text{cm}^{-1}$ , as shown in Figure 1. An extension of the experimental setup it is also discussed to perform four-point transport measurements in tandem with UHV Raman [4].

## References

- [1] Rogge, S., Durkut, M., & Klapwijk, T. M. (2003). Physical Review B, 67(3), 033410.
- [2] Latzke, D. W., Ojeda-Aristizabal, C., Griffin, S. M., Denlinger, J. D., Neaton, J. B., Zettl, A., & Lanzara, A. (2019). Physical Review B, 99(4), 045425.
- [3] Nano Lett. 2018, 18, 9, 6045–6056
- [4] Nature Communications volume 12, Article number: 2542 (2021)

## Figures

**Figure 1:** Raman spectra of Pristine  $C_{60}$  (green),  $Rb_3C_{60}$  (orange) and  $Rb_6C_{60}$  (blue) with green 532nm laser.

